

**Product Specification**

**Silicon NPN Power Transistors**

**2SC2245**

**DESCRIPTION**

- With TO-3 package
- High voltage, high speed

**APPLICATIONS**

- Power switching
- Power amplification
- power driver

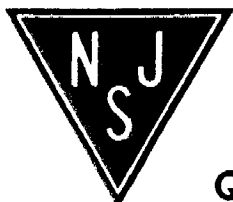
PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Absolute maximum ratings(Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CB0</sub>	Collector-base voltage	Open emitter	450	V
V <sub>CE0</sub>	Collector-emitter voltage	Open base	400	V
V <sub>EB0</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		10	A
I <sub>CM</sub>	Collector current-peak		20	A
P <sub>T</sub>	Total power dissipation	T <sub>mb</sub> =25°C	100	W
T <sub>J</sub>	Junction temperature		200	°C
T <sub>stg</sub>	Storage temperature		-65-200	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th-j-mb</sub>	Thermal resistance from junction to mounting base	1.0	°C/W



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

**Quality Semi-Conductors**

**Silicon NPN Power Transistors**

**2SC2245**

**CHARACTERISTICS**

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE(sus)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.1A ; L=25mH	400			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A; I <sub>B</sub> =0.8A			1.2	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4A; I <sub>B</sub> =0.8A			1.5	V
I <sub>CB0</sub>	Collector cut-off current	V <sub>CB</sub> =450V; I <sub>E</sub> =0 T <sub>C</sub> =125			1 4	mA
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =400V; I <sub>B</sub> =0			5.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			1.0	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =4A ; V <sub>CE</sub> =5V	10			

Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =4A ; I <sub>B1</sub> = I <sub>B2</sub> =0.8A			1.0	μs
t <sub>s</sub>	Storage time				2.0	μs
t <sub>f</sub>	Fall time				1.0	μs

